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1 24. The semiconductor laser diode chip, as claimed in claim 21, wherein said first pair of
2 marks comprises lines formed on an upper portion of said active layer.

1 25. The semiconductor laser diode chip, as claimed in claim 24, wherein said lines have a
2 same width as that of said active layer.

DI 26. The semiconductor laser diode chip, as claimed in claim 21, wherein said second pair of
2 marks have a circular shape.

1 27. The semiconductor laser diode chip, as claimed in claim 21, wherein said pair of
2 substrate side marks have a diameter different than a diameter of said second pair of marks.

DI 28. The semiconductor laser diode chip, as claimed in claim 21, wherein a distance between
2 each individual mark of said first pair of marks is 10 μm .

1 29. An optical module, comprising:
2 a substrate; and
3 the semiconductor laser diode chip of claim 1 formed on the substrate.

1 30. The module of claim 29, further comprising:
2 an optical fiber arranged on the substrate and connected to the semiconductor laser
3 diode chip.

Sub 37 31. A semiconductor laser diode chip to be mounted on a substrate for an optical module,
2 comprising:
3 an active layer;
4 a positioning-type mark in a vicinity of said active layer; and
5 a measurement-type mark located between said active layer and said positioning-type
6 mark.

DI 32. The semiconductor laser diode chip as claimed in claim 31, wherein said chip is
2 positioned on said substrate by aligning said position-type mark with a another position-type
3 mark on said substrate.

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- 1 33. The semiconductor laser diode chip as claimed in claim 32, wherein said chip is
2 positioned on said substrate by measuring a distance between said active layer and said
3 measurement-type mark. —
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